

■ PRODUCT CHARACTERISTICS

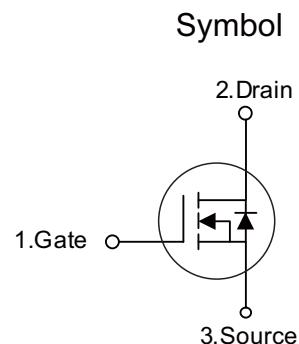
VDSS	60V
R _{DS(on)} Typ(@V _{GS} =10 V)	16mΩ
ID	50A

■ APPLICATIONS

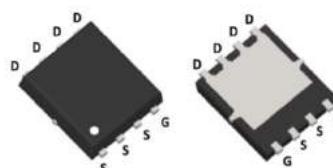
- * Switching applications

■ FEATURES

- * High Switching Speed
- * Improved dv/dt capability



PDFN3333-8L



■ ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	V _{DSS}	60	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current	I _D	50	A
Pulsed Drain Current (Note 2)	I _{DM}	150	A
Avalanche Energy Single Pulsed (Note 3)	E _{AS}	92	mJ
Peak Diode Recovery dv/dt	dv/dt	10	V/ns
Power Dissipation	P _D	46	W
Junction Temperature	T _J	+150	°C
Operation and Storage Temperature	T _{STG}	-55 ~ +150	°C

Notes:

1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by maximum junction temperature.

3. L=43mH, I_{AS}=43A, V_{DD}=25V, R_G=20Ω, Starting T_J=25°C

4. I_{SD} ≤ 30A, V_{DS}=0V, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C

■ THERMAL DATA

PARAMETER	SYMBOL	RATING	UNIT
Junction to Ambient	θ _{JA}	100	°C/W
Junction to Case	θ _{JC}	2.7	°C/W

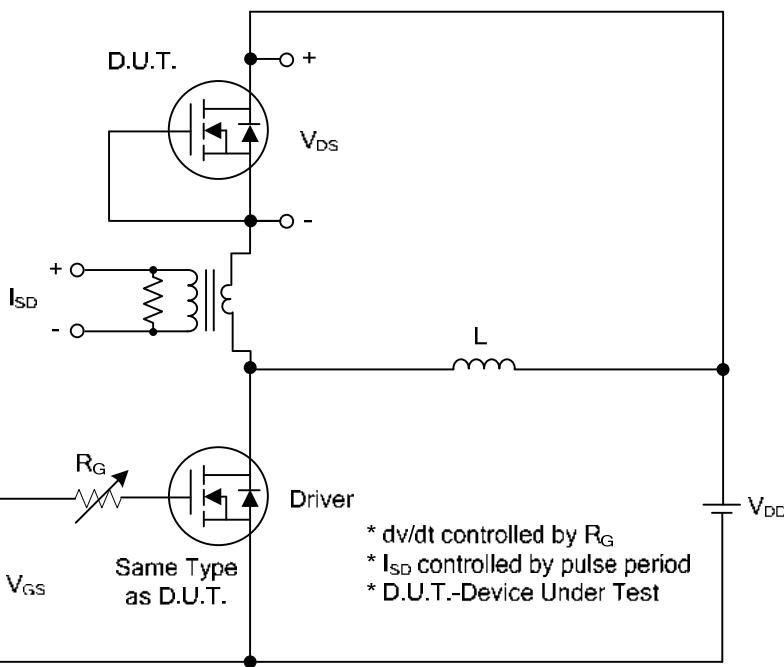
■ ELECTRICAL CHARACTERISTICS (T_c=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	60			V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V			10	μA
Gate-Source Leakage Current	Forward	V _{GS} =20V, V _{DS} =0V			100	nA
	Reverse	V _{GS} =-20V, V _{DS} =0V			-100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250μA	1.0		2.5	V
Static Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =25A		16	20	mΩ
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{ISS}	V _{GS} =0V, V _{DS} =25V, f=1MHz		2500		pF
Output Capacitance	C _{OSS}			230		pF
Reverse Transfer Capacitance	C _{RSS}			200		pF
SWITCHING CHARACTERISTICS						
Total Gate Charge	Q _G	V _{DS} =50V, V _{GS} =10V, I _D =1.3A I _G =3mA (Note1,2)		7.2		nC
Gate-Source Charge	Q _{GS}			0.4		nC
Gate-Drain Charge	Q _{GD}			0.8		nC
Turn-On Delay Time	t _{D(ON)}	V _{DS} =30V, V _{GS} =10V, I _D =50A, R _G =25Ω (Note1,2)		18		ns
Turn-On Rise Time	t _R			46		ns
Turn-Off Delay Time	t _{D(OFF)}			202		ns
Turn-Off Fall Time	t _F			116		ns
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Maximum Continuous Drain-Source Diode Forward Current	I _S				50	A
Maximum Pulsed Drain-Source Diode Forward Current	I _{SM}				150	A
Drain-Source Diode Forward Voltage	V _{SD}	I _S =50A, V _{GS} =0V			1.5	V
Body Diode Reverse Recovery Time	t _{rr}	I _S =30A, V _{GS} =0V, dI _S /dt=100A/μs		50		ns
Body Diode Reverse Recovery Charge	Q _{rr}			80		nC

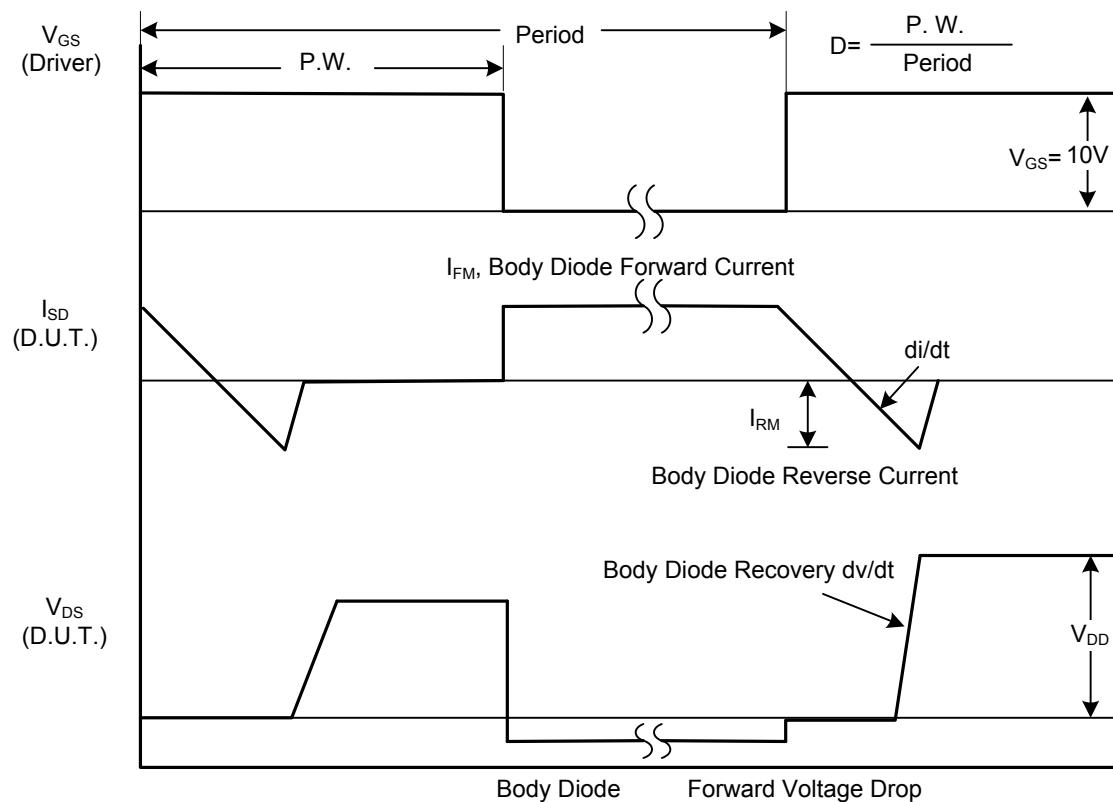
Notes: 1. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.

2. Essentially independent of operating temperature.

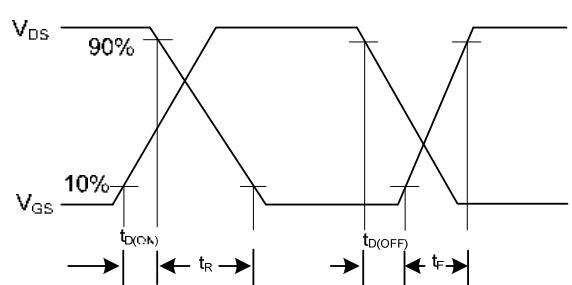
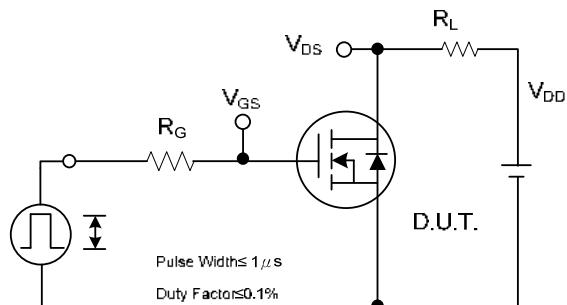
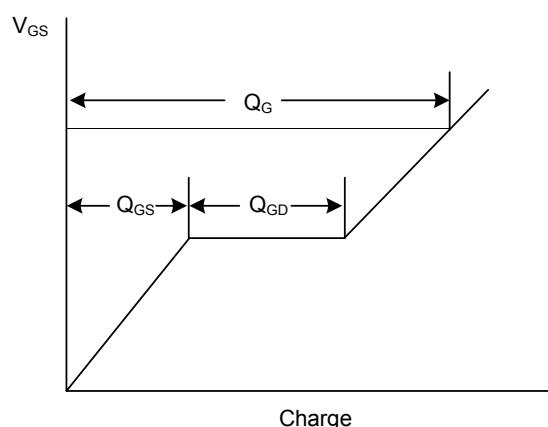
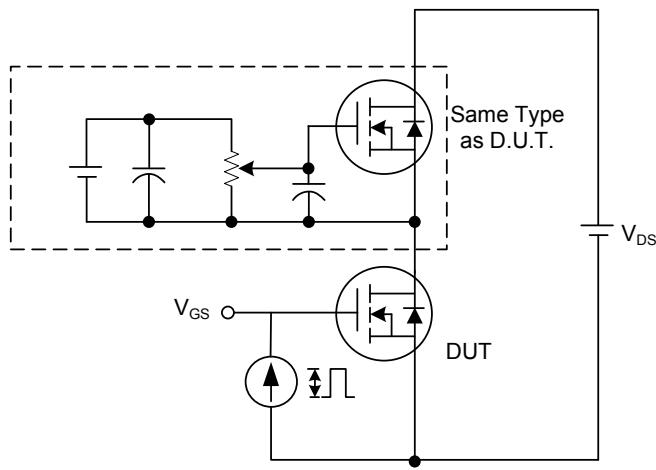
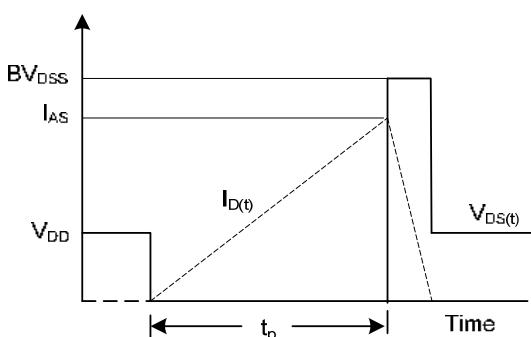
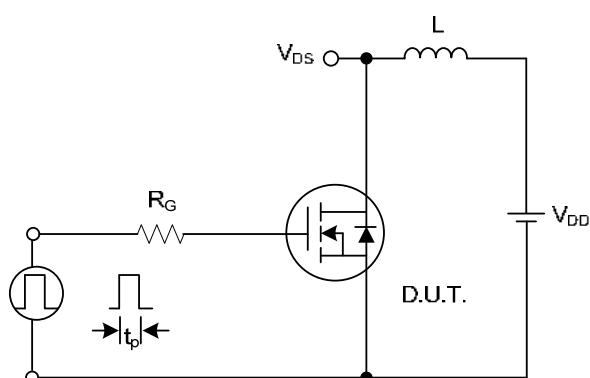
■ TEST CIRCUITS AND WAVEFORMS



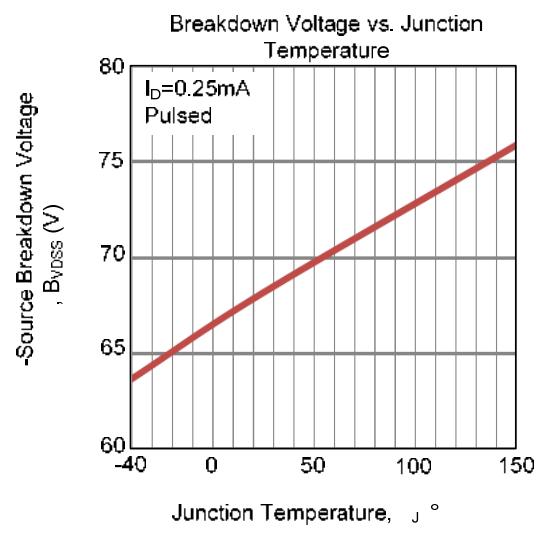
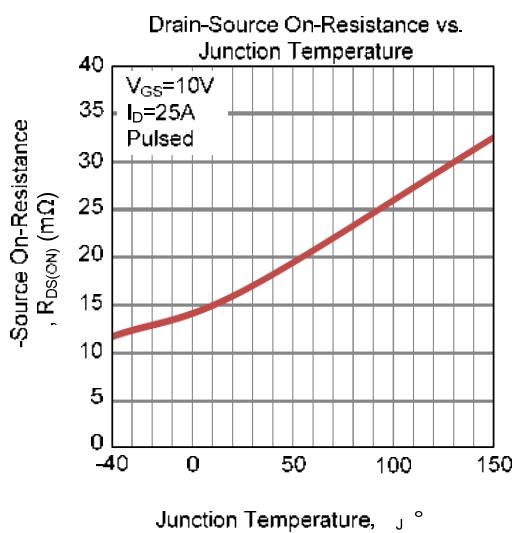
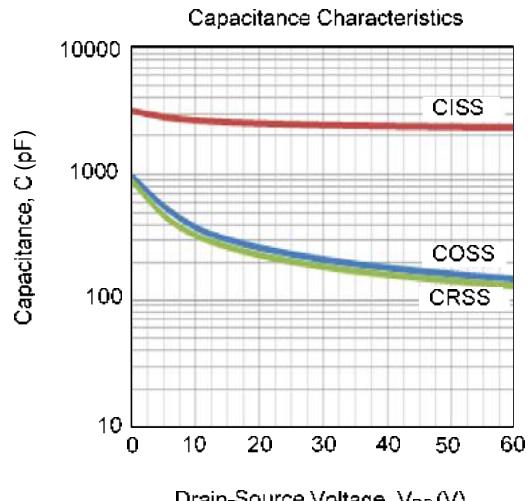
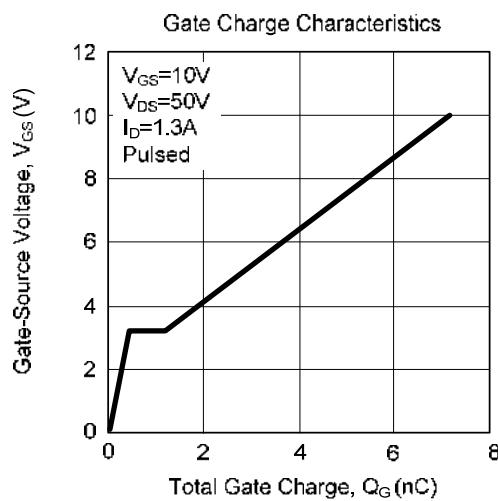
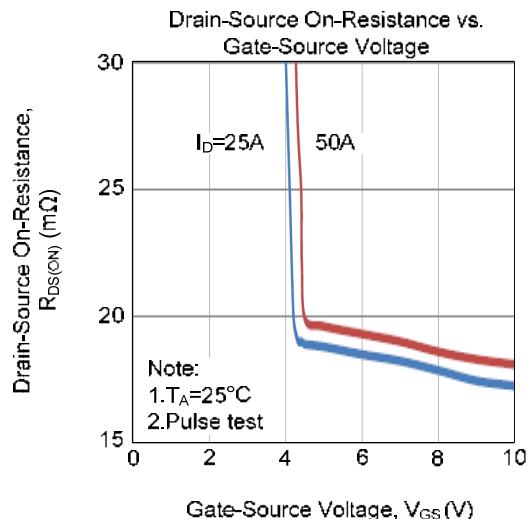
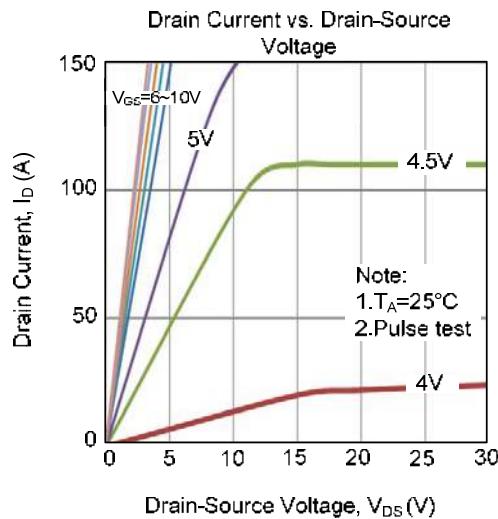
Peak Diode Recovery dv/dt Test Circuit



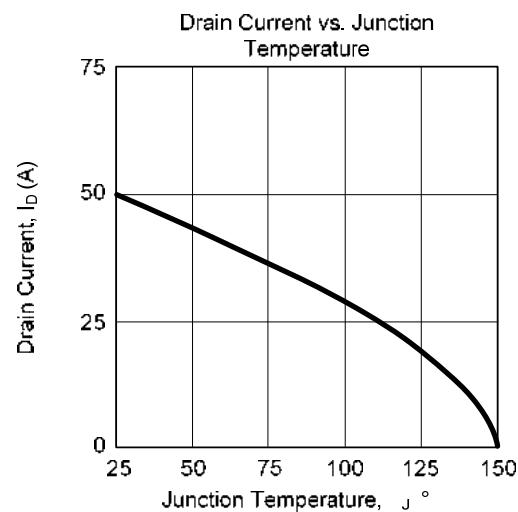
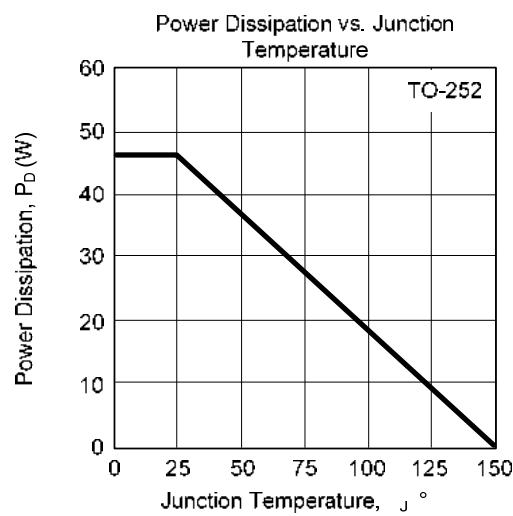
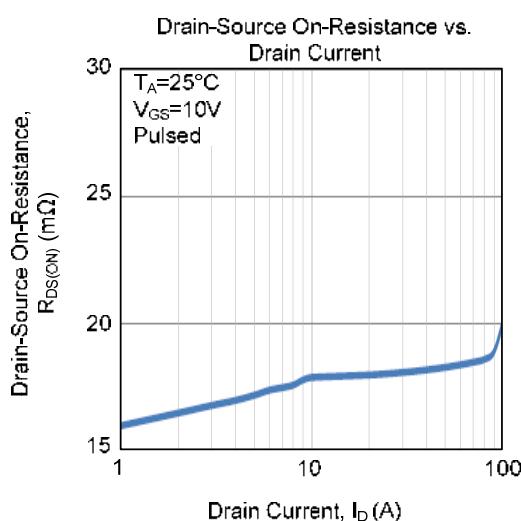
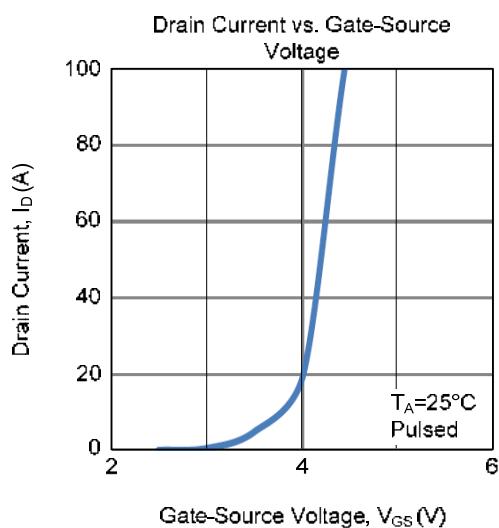
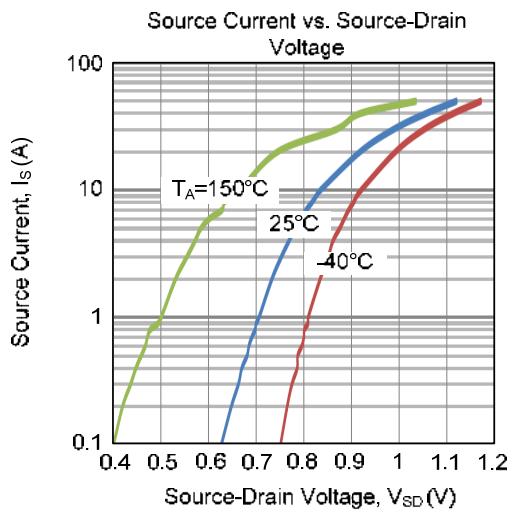
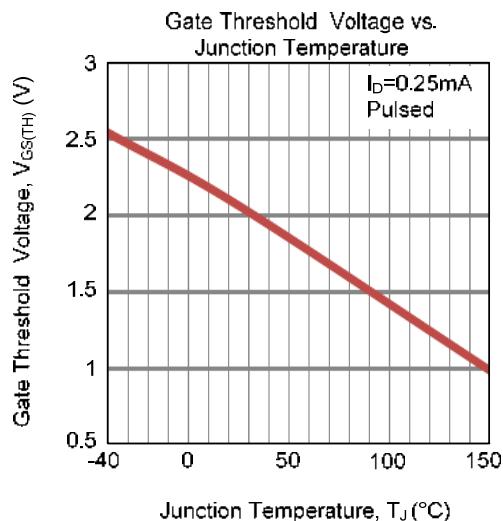
Peak Diode Recovery dv/dt Waveforms

■ TEST CIRCUITS AND WAVEFORMS(Cont.)

Fig. 2A Switching Test Circuit
Fig. 2B Switching Waveforms

Fig. 3A Gate Charge Test Circuit
Fig. 3B Gate Charge Waveform

Fig. 4A Unclamped Inductive Switching Test Circuit
Fig. 4B Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS(Cont.)



■ PDFN3333-8L Package Mechanical Data

